

V_{DS}	20V
I_b	80A
$R_{DS(on)}$ (at $V_{GS} = 4.5V$)	18mΩ
$R_{DS(on)}$ (at $V_{GS} = 2.5V$)	22mΩ
$R_{DS(on)}$ (at $V_{GS} = 1.8V$)	30mΩ

Trench Power LV MOSFET technology
 High density cell design for low $R_{DS(on)}$
 High Speed switching

Battery protection
 Load switch
 Power management

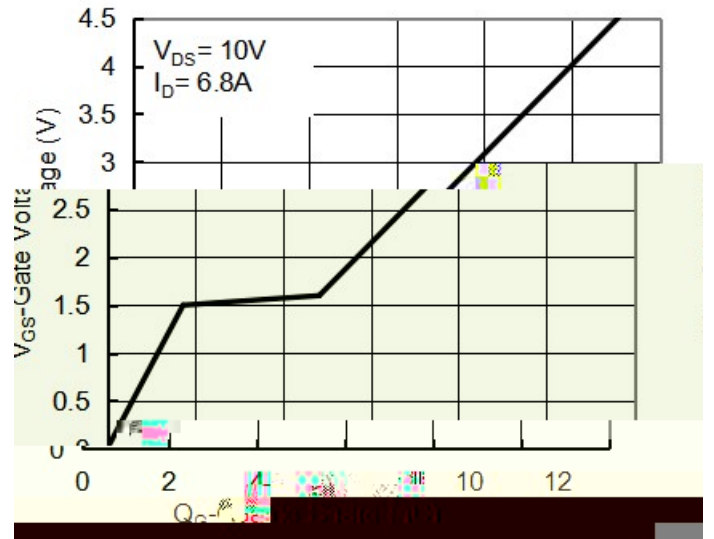
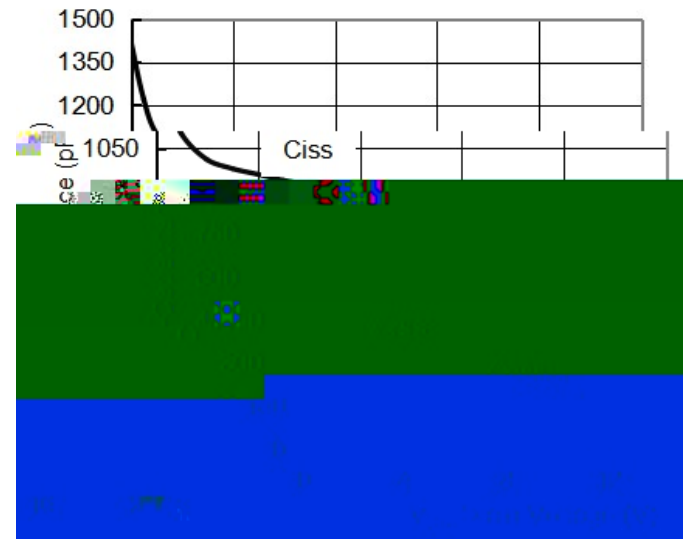
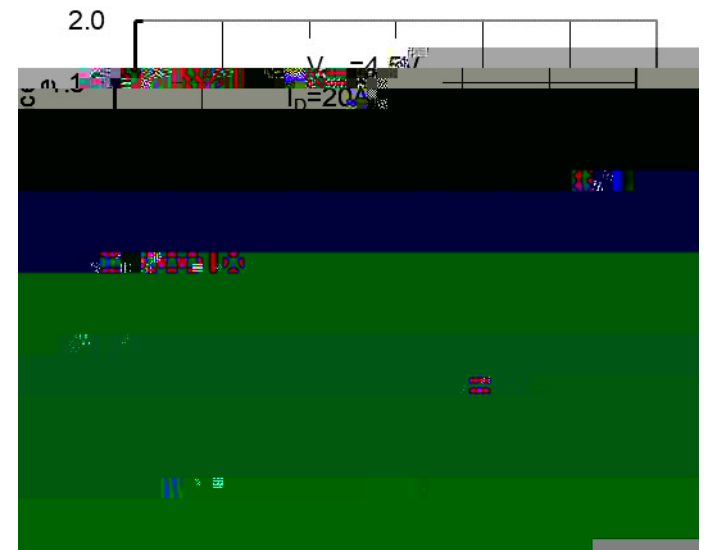
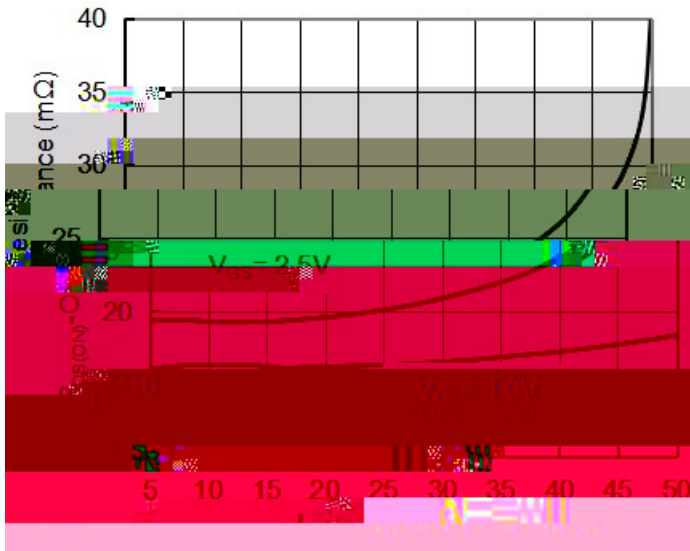
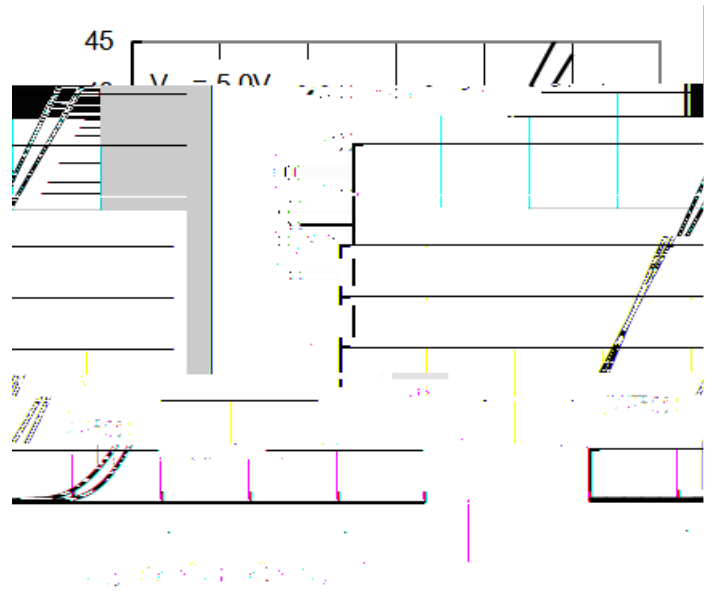
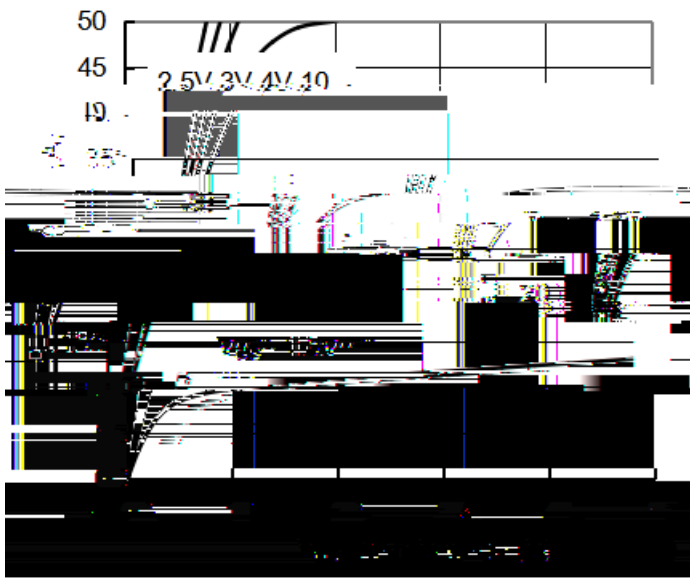
($T_A = 25$ unless otherwise noted)

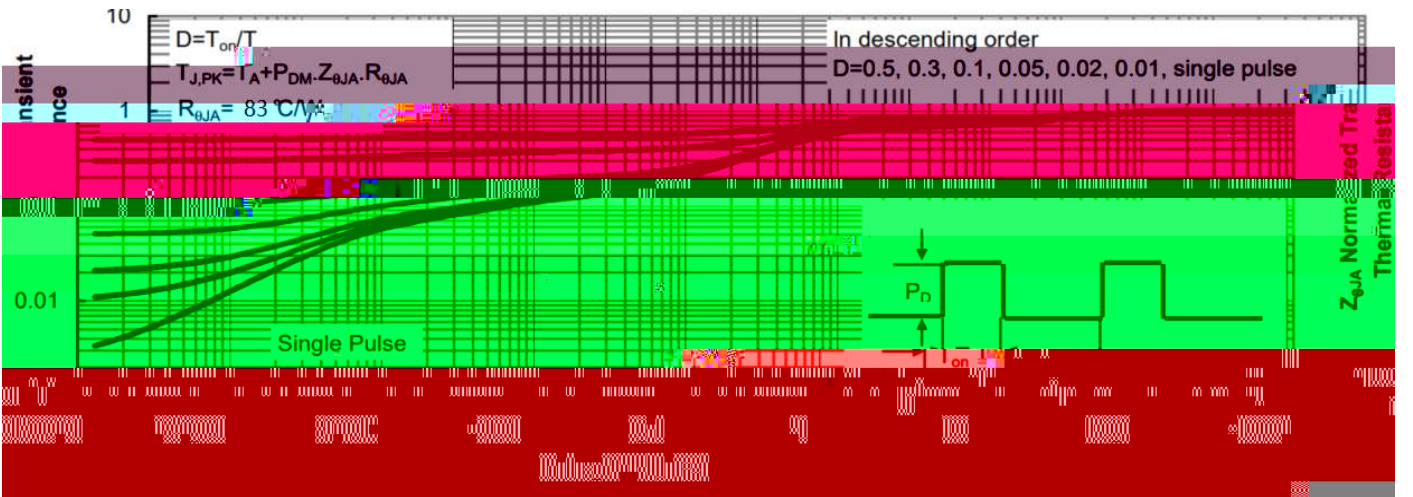
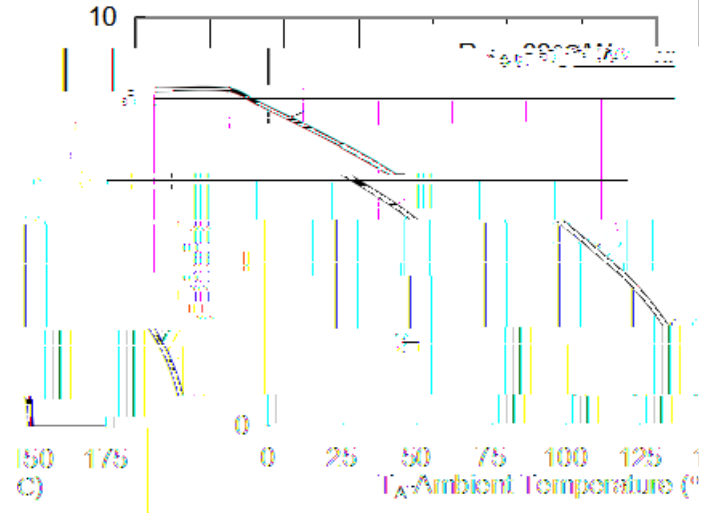
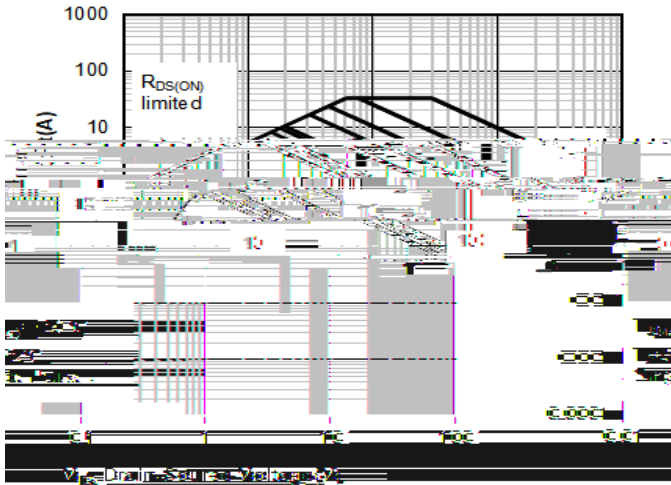
Drain-source Voltage	V_{DS}	20	V
Gate-source Voltage	V_{GS}	10	V
Drain Current	I_b	8	% A

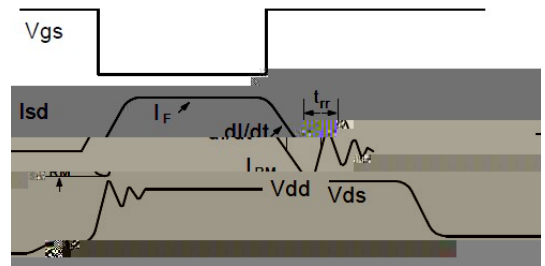
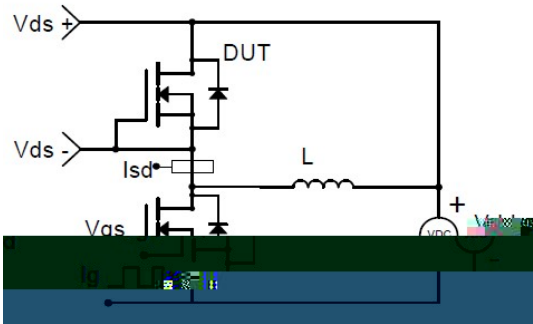
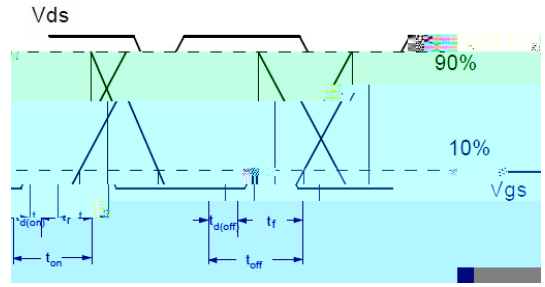
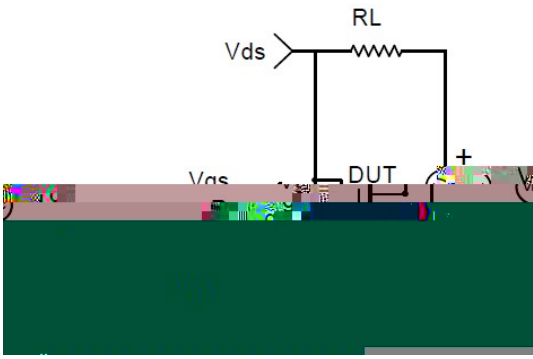


(T_F=25 unless otherwise noted)

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